Tektronix

Wide Band Gap for Power Converters (SiC / GaN vs Si)

PAT HENSLEY AMERICAS BUSINESS DEVELOPMENT MANAGER AUTOMOTIVE AND ENERGY

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Agenda

- Introduction Power Challenges
- Wide Band Gap (GaN / SiC)
- Measurements
 - Challenges
 - Solutions
- Summary

Why Sic and Gan vs Si?

/ER DENSITY Stability Weight



Traditional Circuit Gets Complicated

THE HALF BRIDGE

- Demands for higher efficiency
- Increased voltages and currents
- Smaller size
- Environmental tolerance
- Cost

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• Reliability



Technology is Changing

Wide Band Gap (GaN / SiC)



Introduction of Wide Band Gap (GaN / SiC)

- GaN: Gallium Nitride
- SiC: Silicon Carbide

Compared to conventional semiconductor materials like Silicon (Si) and Gallium Arsenide (GaAs) wide-bandgap semiconductors allow:

- Operation at much higher voltage/current
- Operation at higher temperatures
- Operation at higher frequencies
- Smaller packaging





Power vs. Switching Speeds



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More Than Just Switching Frequency

FOCUSING ON RISETIMES

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Measurement Challenges



Wide Band Gap: Measurement Challenges

Fast high voltage fast switching

- Common mode rejection
- Fast rise times
- Measurement bandwidth
- Sensitivity to parasitics
- Measurements that don't effect the design
- Accessibility to test points
- Connecting to the small model sizes
 Safety
- Injury or death





Challenges (headaches) with WBG



- Low Loss High-Speed Switching Switching High Switching Interview (small size, large capacity) High Operating Interview (small size, large capacity)
- Alternative packaging materials
- EMI
- New designs, new architectures
- PCB layout
- Integration with existing systems or new Gate Driver
- Reliability and Robustness
- \$\$\$
- Simulate & Measure



High Side Measurement Challenge REJECTING COMMON MODE VOLTAGE INDUCTED ERRORS

· Isolation from ground

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• Fast hi-fidelity measurement system







Switching faster (and its consequences)

High Switching Speed (dv/dt and di/dt) - Oscillations



Real? Or measurement artifact?

From Infineon Presentation



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Bandwidth and Rise Time Considerations

RISE TIME, NOT SWITCHING SPEED

- Edge rate
- Ringing

• Sharp transients



Ringing

Safety: High voltage precautions





Switching losses and deskew





Switch Voltage and Current



Switch Power Loss



Connection Fidelity and Safety

ISSUES WITH THIS SETUP FOR WBG?



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SiC Vgs High Side Comparision

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Recap in a nutshell



Fast switching -> more parasitic Reduce current loops, reduce resonances Accurate measurements rely on using suitable instruments (for that specific measurement) Instrument starts at the probe tip

Instruments always influence measurements

Stay safe

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IsoVu Probing Technology

IsoVu[™] technology is a radically new high voltage isolated differential probing solution that gives **Accurate** and **Repeatable** results

- Galvanically isolates the device-under-test from a Tektronix oscilloscope.
- 1 GHz bandwidth
- World's best common mode rejection
 - Up to **160 dB** (100 million to 1)
- > 2.5 kV differential voltage range
- 60 kV common mode voltage range
- Up to $40 \text{ M}\Omega$ input resistance





MMCX For Isovu And Passive Probes

HI-FIDELITY, SAFE, RELIABLE



206-0663-xx



Characterize the Entire Switching Circuit IT IS CRITICAL TO SEE THESE TEST POINTS

- · Characterize the gate voltages, Vds, and Is
- Characterize the time alignment of high and low side events
- Optimize and tune switching characteristics

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Thank You